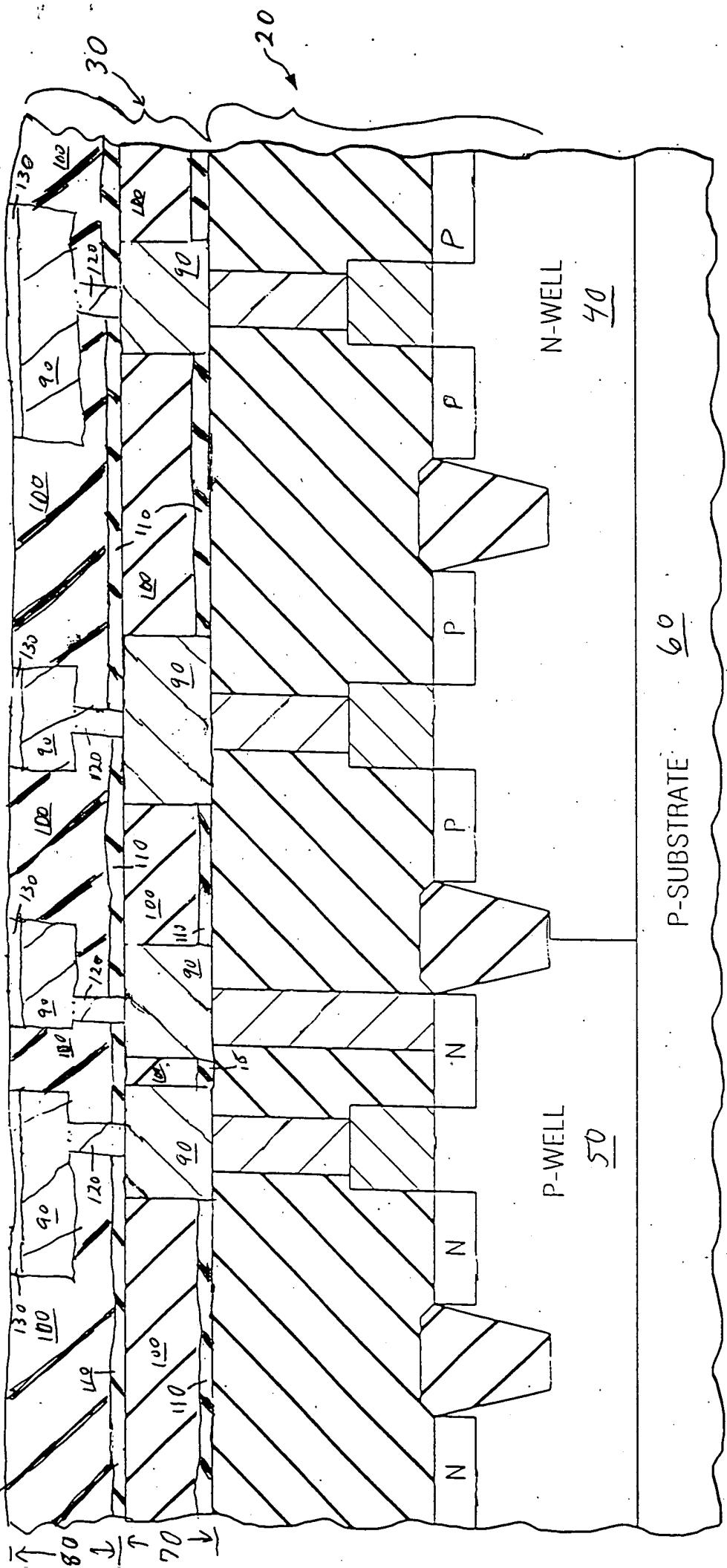


TI -35330
RHK

10



FI 6.1

200 - Formation of barrier layer
(optional)

210 - Formation of dielectric layer

220 - Pattern & etch of dielectric layer and ~~remove~~ the barrier layer (if used)

230 - Barrier metal and Copper deposition

240 - Copper CMP

260 - Post-CMP clean

280 - Formation of next dielectric layer

TI-35330
RAK

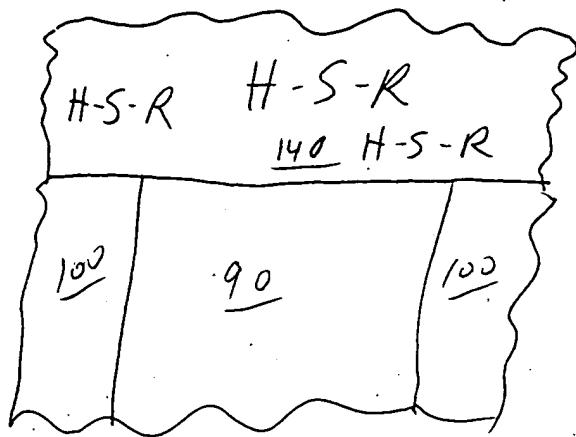


FIG. 3A

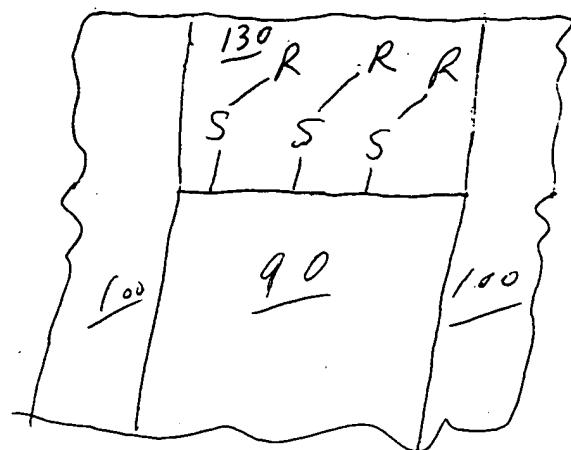


FIG. 3B

TI-35330
RHK

10

二〇

$\leftarrow 80 \rightarrow | \uparrow \leftarrow 70 \rightarrow$

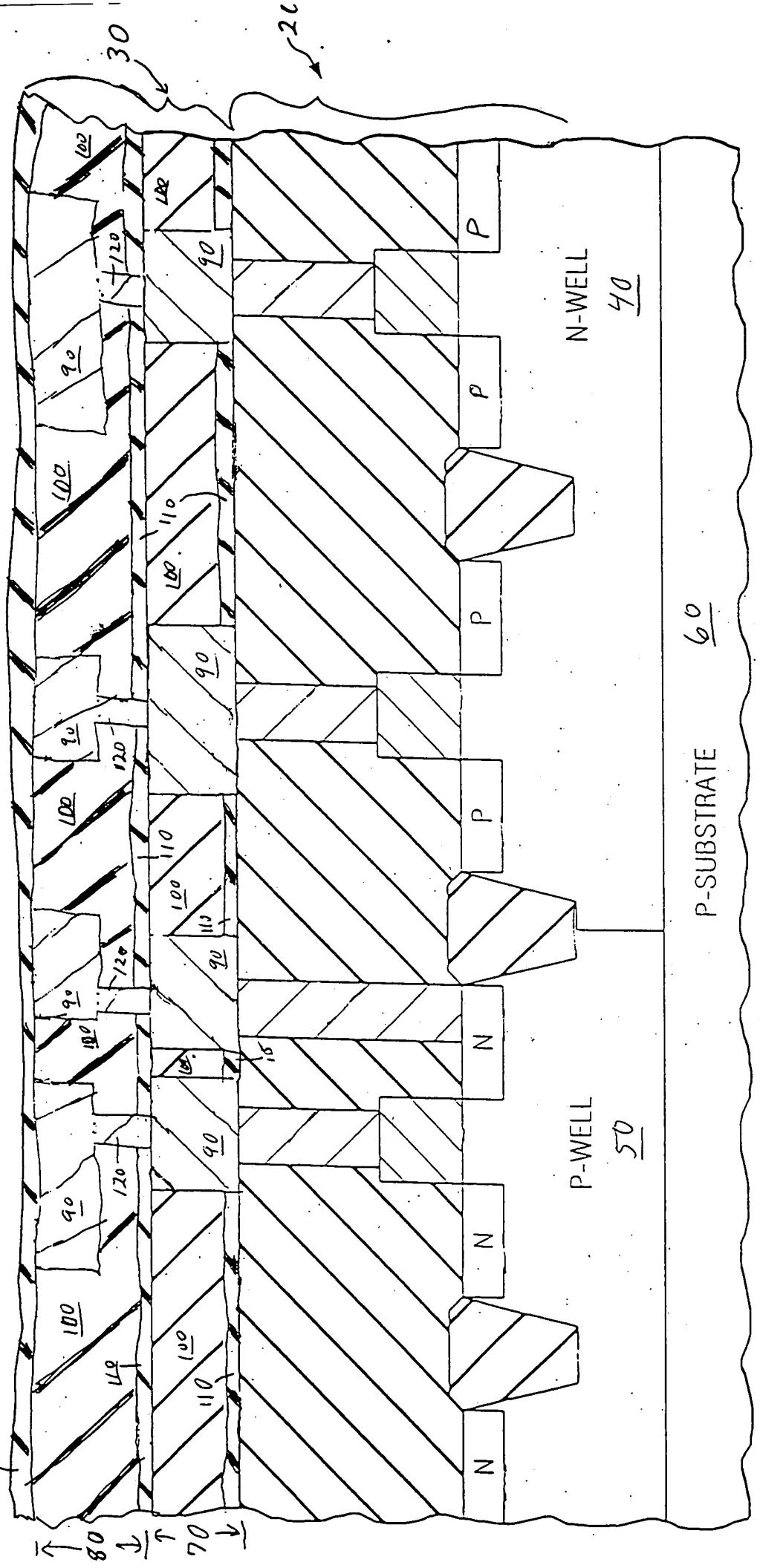


FIG. 4